

2SJ194

P-Channel MOS Silicon FET

Very High-Speed Switching Applications

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

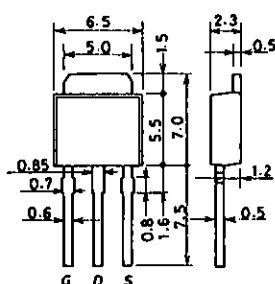
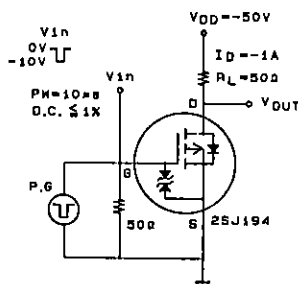
unit

Drain to Source Voltage	V_{DSS}	-100	V
Gate to Source Voltage	V_{GSS}	± 15	V
Drain Current(DC)	I_D	-2	A
Drain Current(Pulse)	I_{DP}	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	-8 A
Allowable Power Dissipation	P_D	$T_c = 25^\circ C$	20 W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

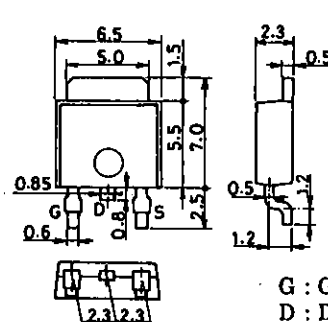
min	typ	max	unit
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D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}, V_{GS} = 0$	-100		V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu\text{A}, V_{DS} = 0$	± 15		V
Zero Gate Voltage	I_{DSS}	$V_{DS} = -100\text{V}, V_{GS} = 0$		-100	μA
Drain Current					
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12\text{V}, V_{DS} = 0$		± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-1.0	-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10\text{V}, I_D = -1\text{A}$	1.2	2	S
Static Drain to Source	$R_{DS(on)}$	$I_D = -1\text{A}, V_{GS} = -10\text{V}$		0.7 0.95	Ω
on State Resistance	$R_{DS(on)}$	$I_D = -1\text{A}, V_{GS} = -4\text{V}$		0.95 1.3	Ω
Input Capacitance	C_{iss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		380	pF
Output Capacitance	C_{oss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		100	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		20	pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		12	ns
Rise Time	t_r	"		14	ns
Turn-OFF Delay Time	$t_{d(off)}$	"		75	ns
Fall Time	t_f	"		40	ns
Diode Forward Voltage	V_{SD}	$I_S = -2\text{A}, V_{GS} = 0$	-1.0	-1.5	V

Package Dimensions 2092A
(unit : mm)



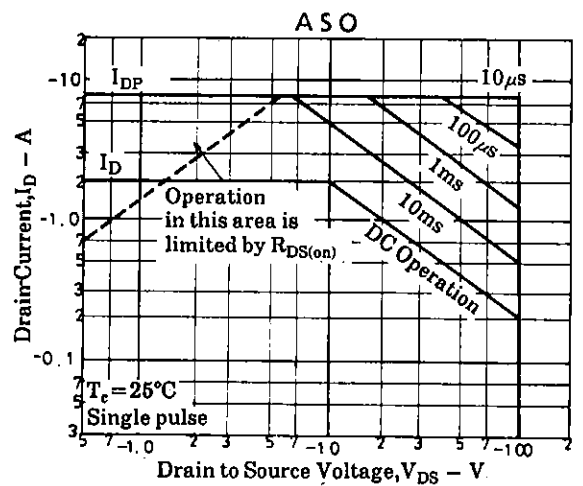
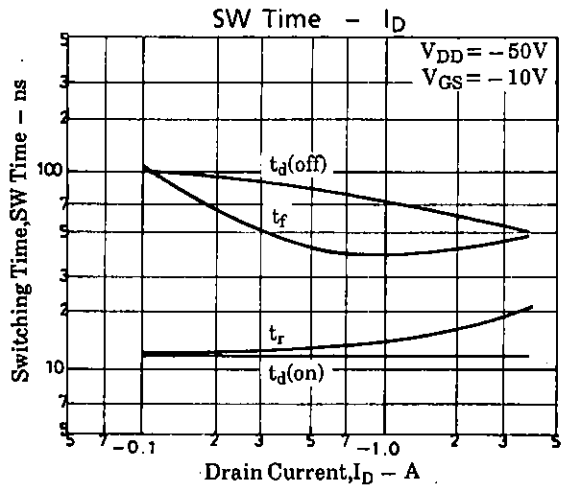
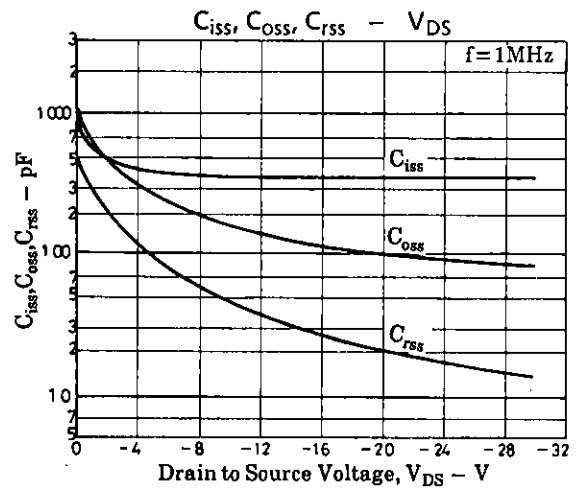
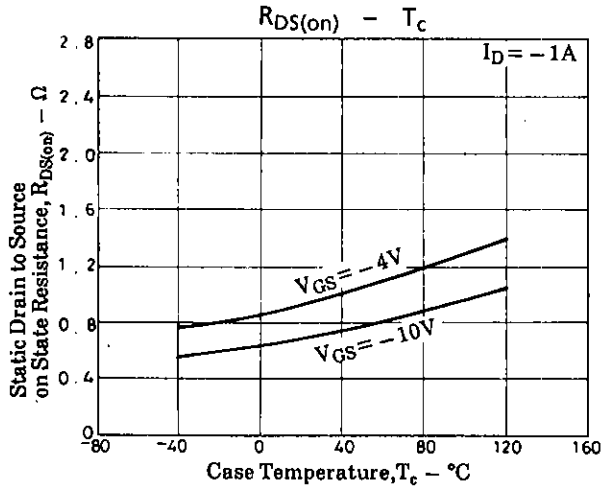
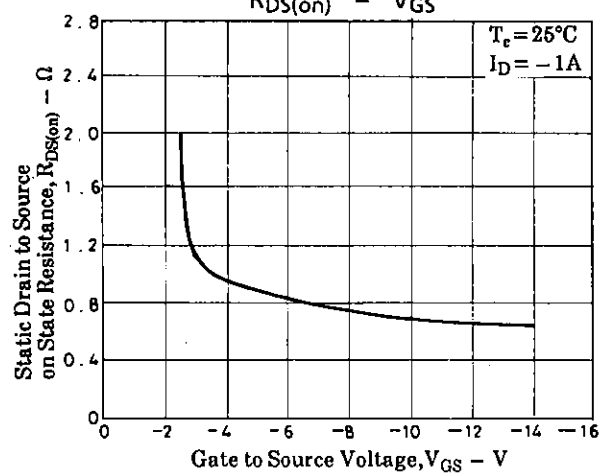
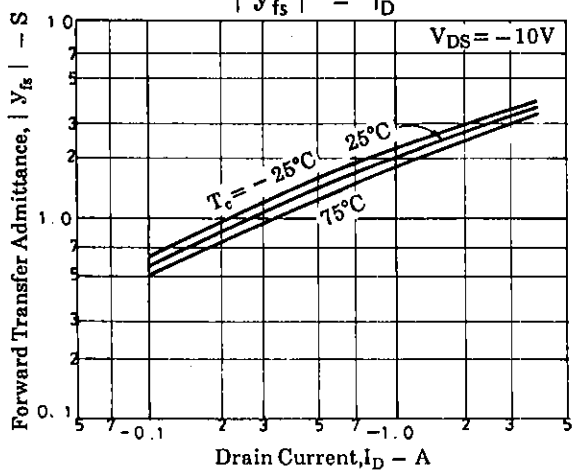
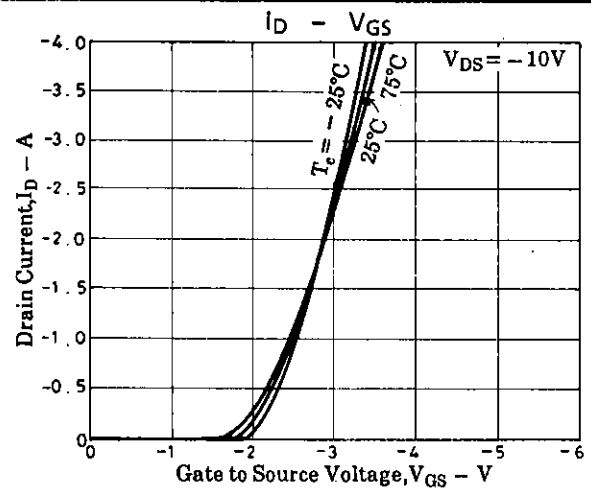
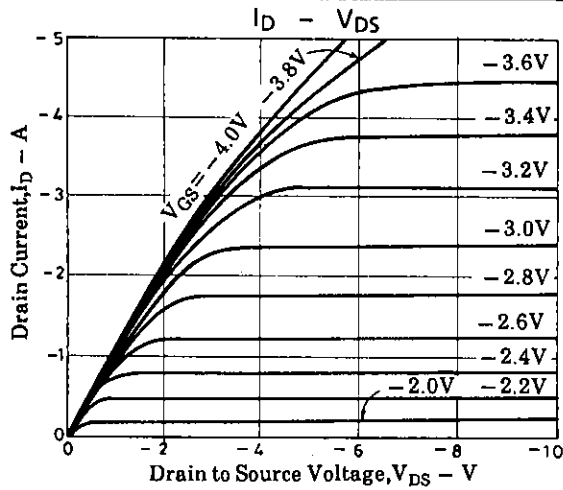
G : Gate
D : Drain
S : Source
SANYO : TP

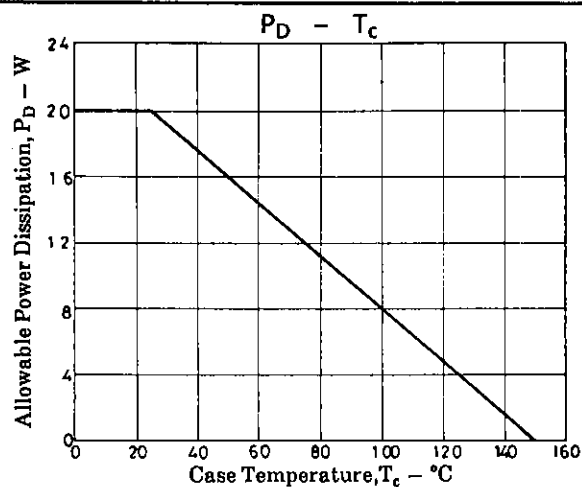


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SANYO : TP - FA

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